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Inventor: Aratani et al.

Examiner: R. McDonald

Serial No.: 09/429,719

Group Unit: 1753

Title: Thin Film Formation Use ...

Atty. Docket No. 9792486-0100

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Response "E" to Final Office Action After RCE Filing

In response to the Final Office Action dated 26 April 2002, the applicants respond as follows.

A. In the Claims, please amend as follows:

DI 17. (amended) A method of forming a thin film comprising the step of: forming an AgPd alloy thin film using a sputtering target material, the AgPd alloy thin film comprising Pd in an amount ranging from 0.5 to 4.9 atomic % and Cu in an amount ranging from 0.1 to 3.5 atomic %; and irradiating an information recording layer with a light beam having a wavelength less than or equal to 650 nm.

18. The method of claim 17, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms.

19. Canceled.

20. The method of claim 17, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms; and wherein the wavelength is less than or equal to 650 nm.

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21. A method of forming a thin film comprising the step of: forming an AgPdTi alloy thin film using a sputtering target material, the AgPdTi alloy comprising Pd in an amount ranging from 0.1 to 1.5 atomic %, Ti in an amount ranging from 0.1 to 2.9 atomic %, and Cu in an amount ranging from 0.1 to 3.5 atomic %.

22. The method of claim 21, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms.

23. The method of claim 21, wherein the wavelength is less than or equal to 650 nm.

24. The method of claim 21, wherein the thin film has a thickness from approximately 500 Angstroms to approximately 1500 Angstroms; and wherein the wavelength is less than or equal to 650 nm.